

Detective Quantum Efficiency of Photon-Counting Detectors Having Edge-on Geometry under Mammography Imaging Condition



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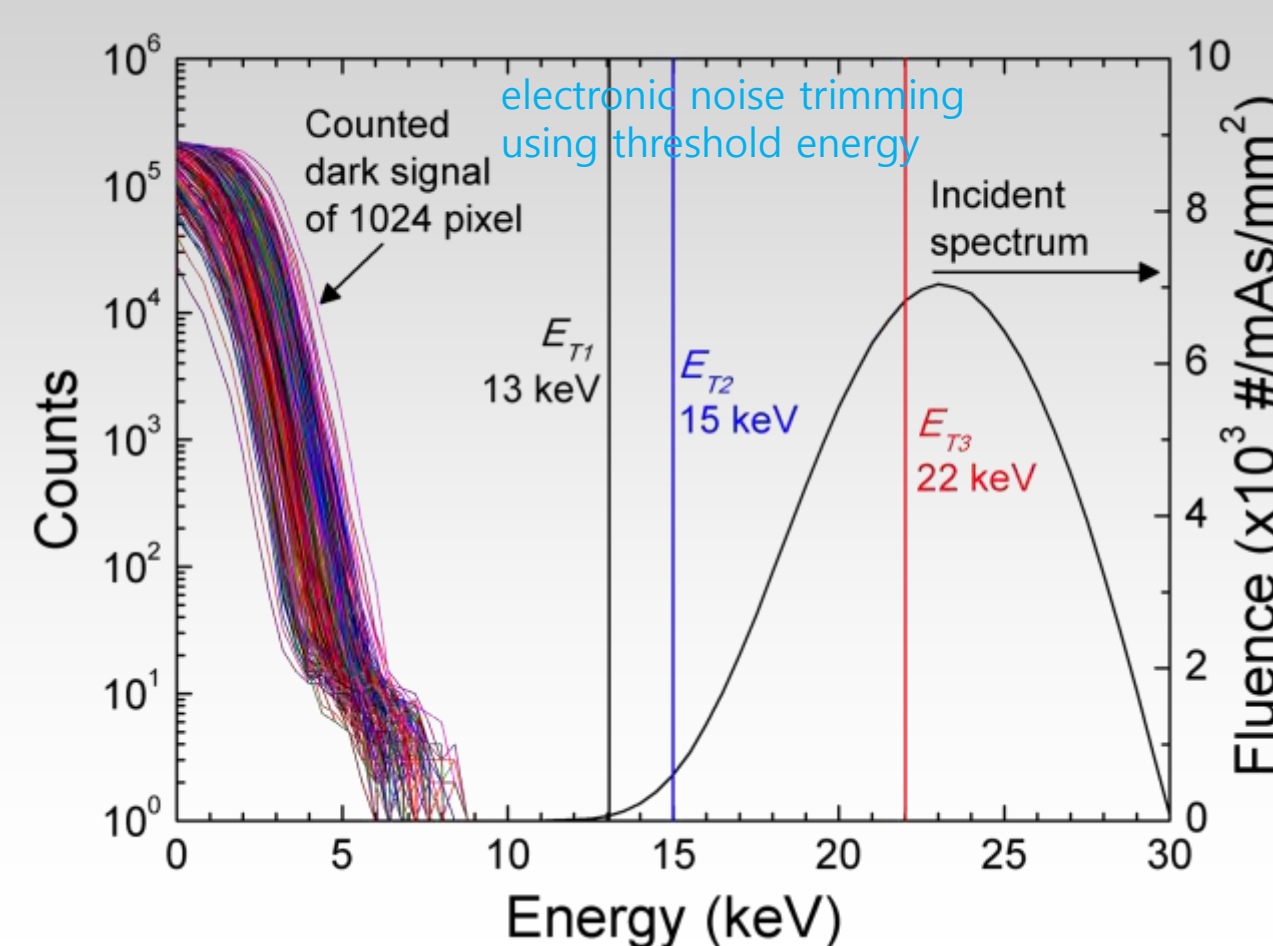
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Motivation

- Compared to the conventional detectors operated in energy-integration mode, the photon-counting operation has several potential advantages;
 - can **suppress electronic noise** by thresholding
 - can obtain **high SNR** (signal-to-noise ratio) images with a lower dose
 - has **linear response** and (theoretically) **infinite dynamic range**
 - has a potential for removing Compton-scattered and fluorescence x-rays in images
 - can **maximize the imaging performance** by energy weighting for each imaging task

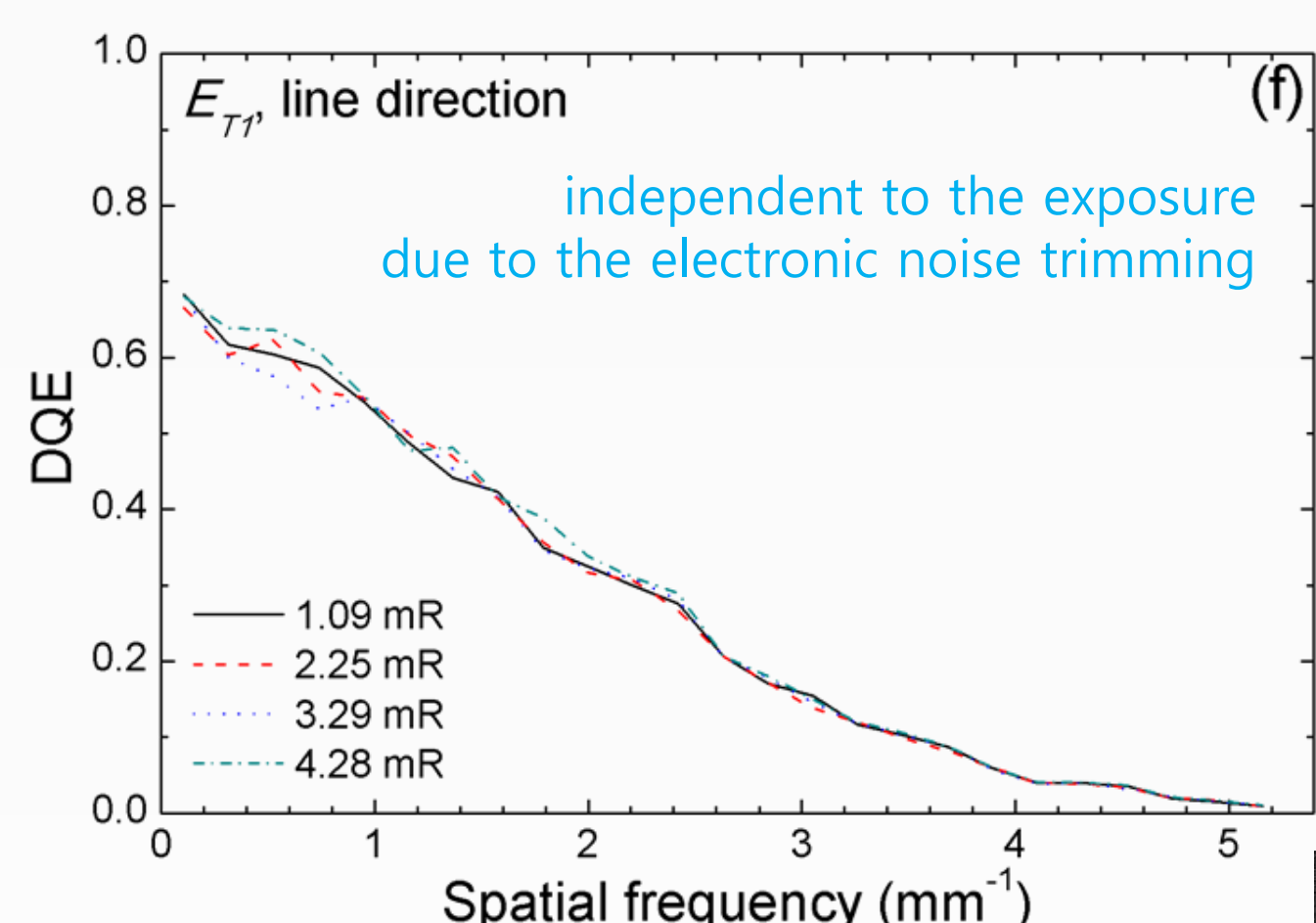
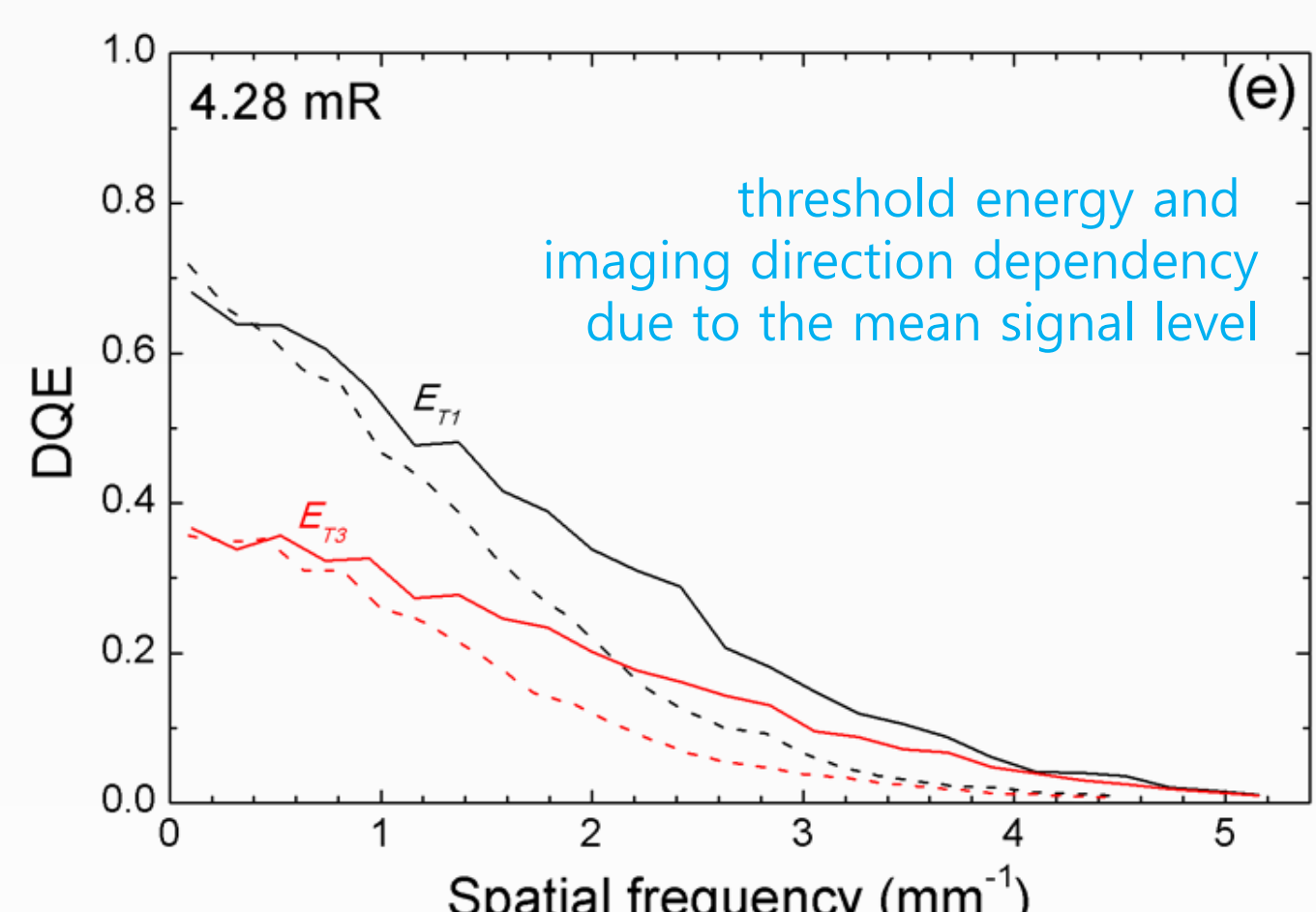
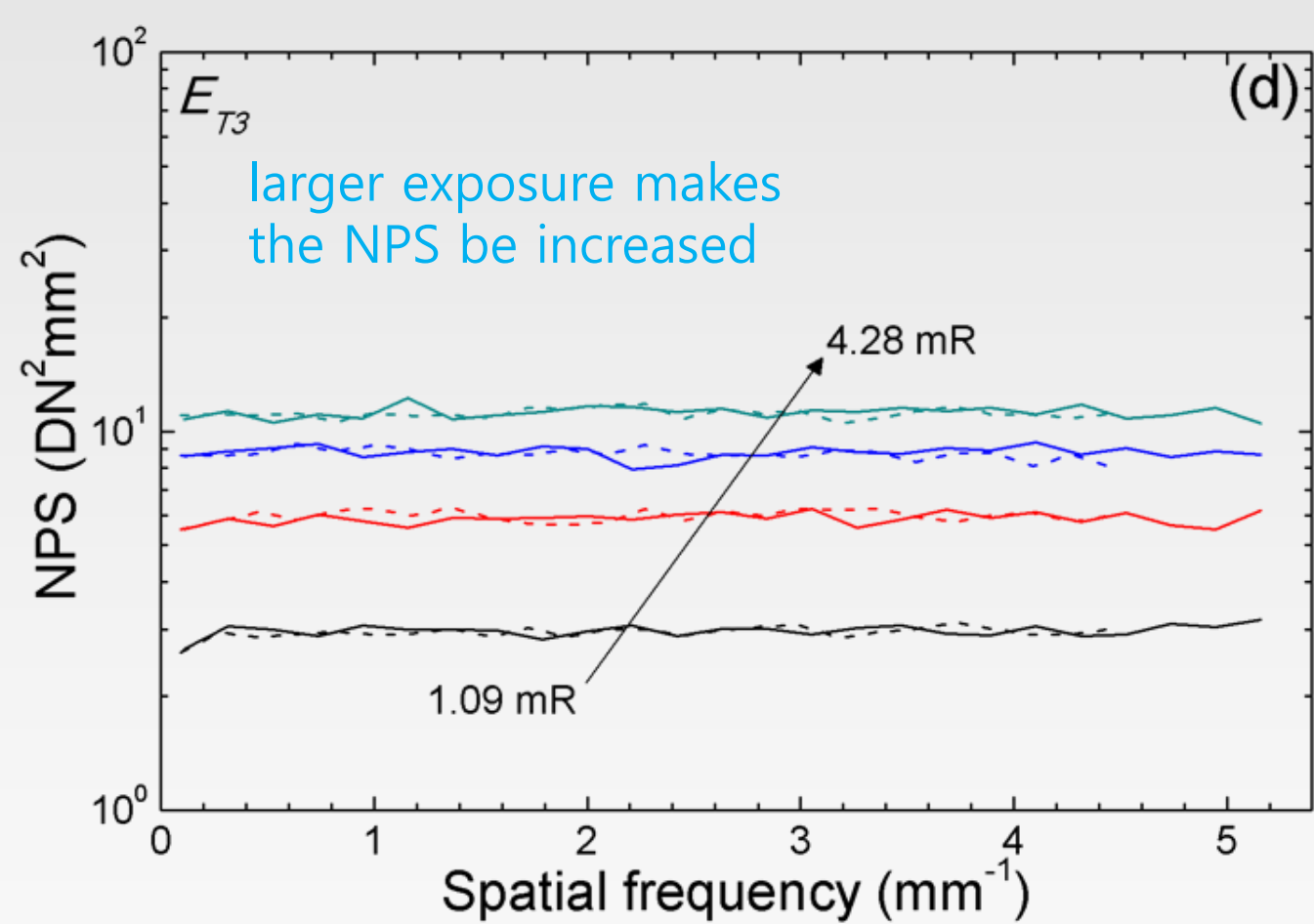
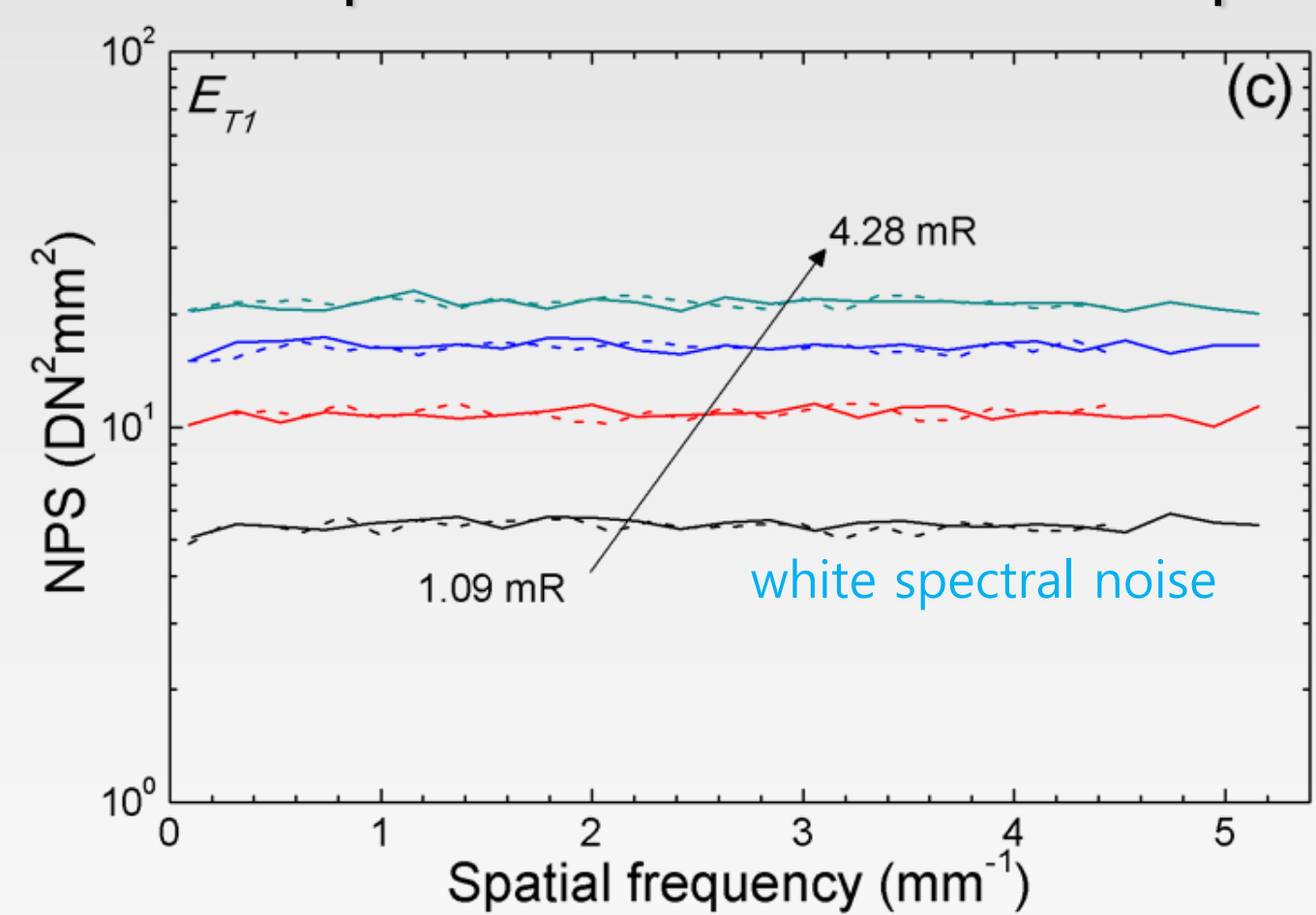
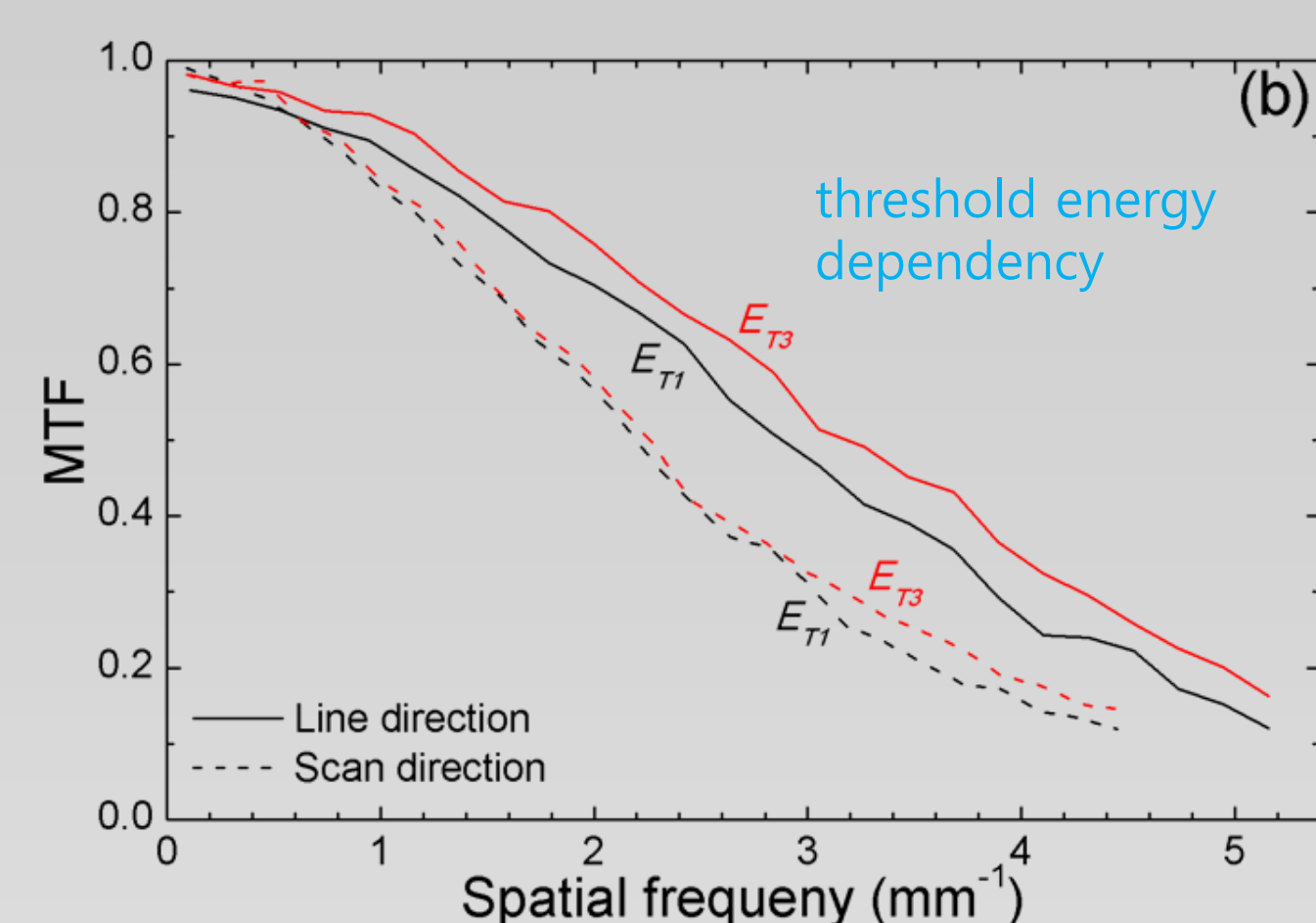
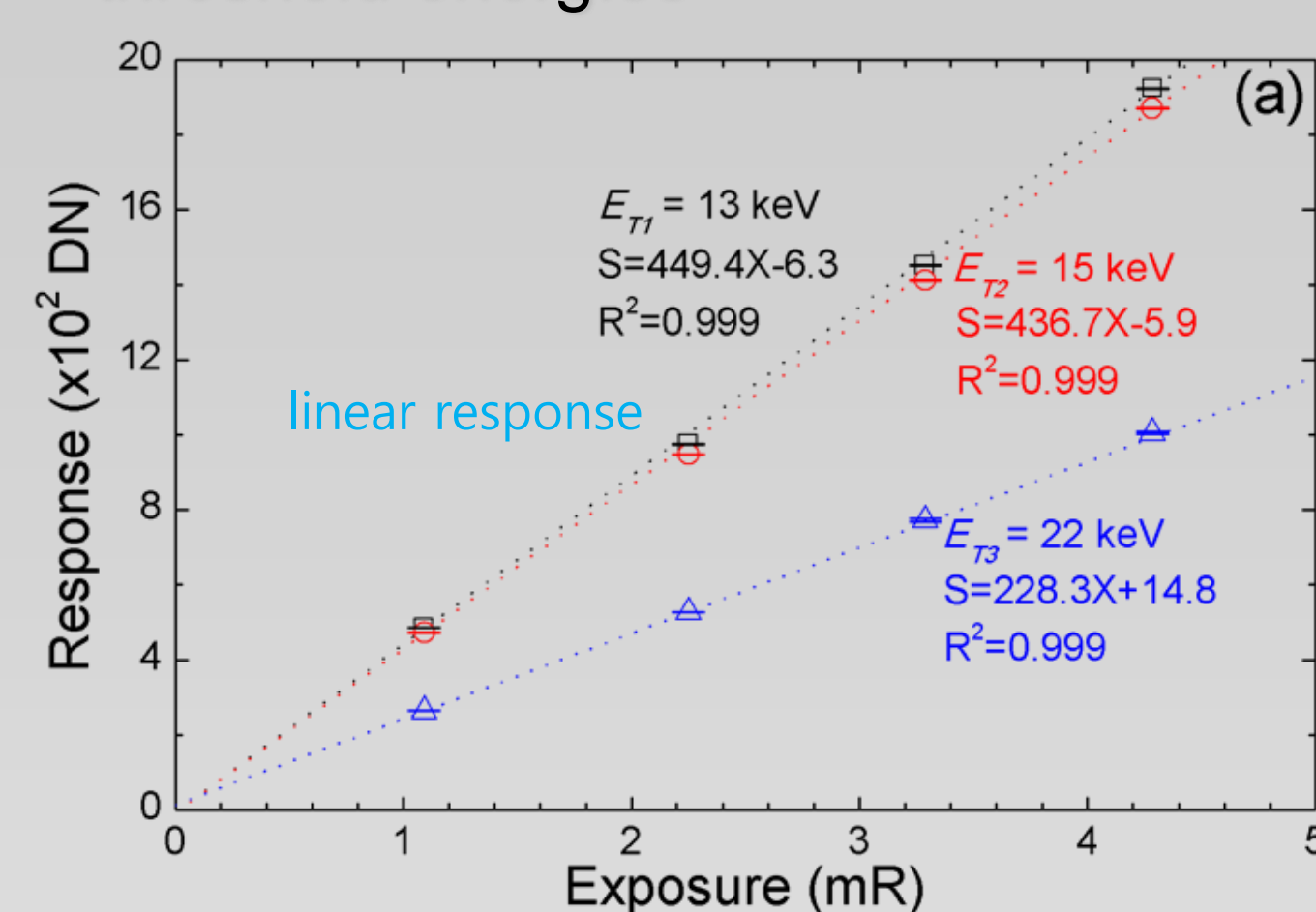


Objectives

- To measure the physical characteristics of the microstrip detector having edge-on geometry operated in **photon counting mode under mammography imaging condition** recommended by the IEC (international electrotechnical commission) regulation (W/AI spectrum).
- To analyze the imaging performances of the microstrip silicon detector in terms of **MTF** (modulation-transfer function), **NPS** (noise-power spectrum), and **DQE** (detective quantum efficiency).

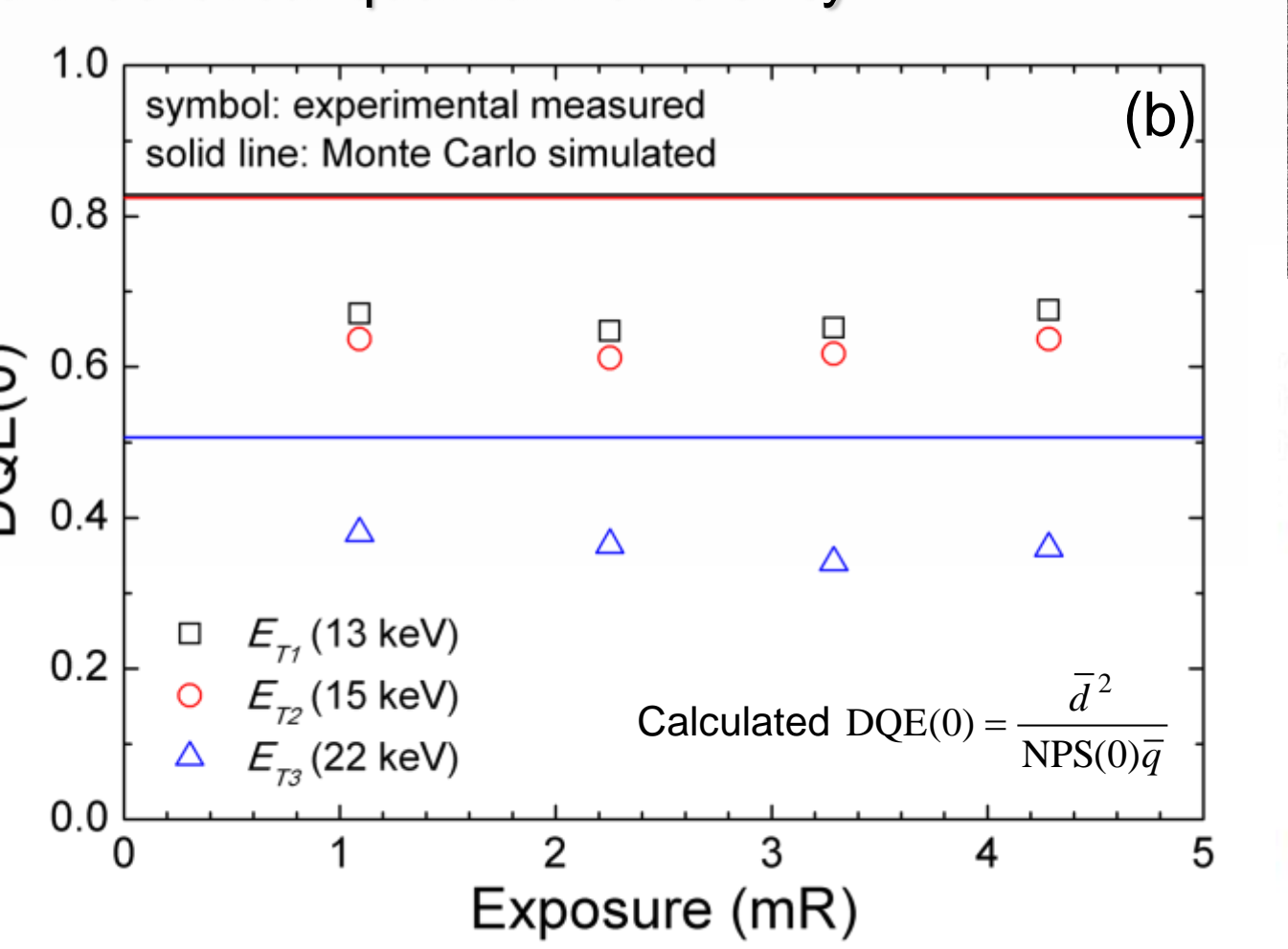
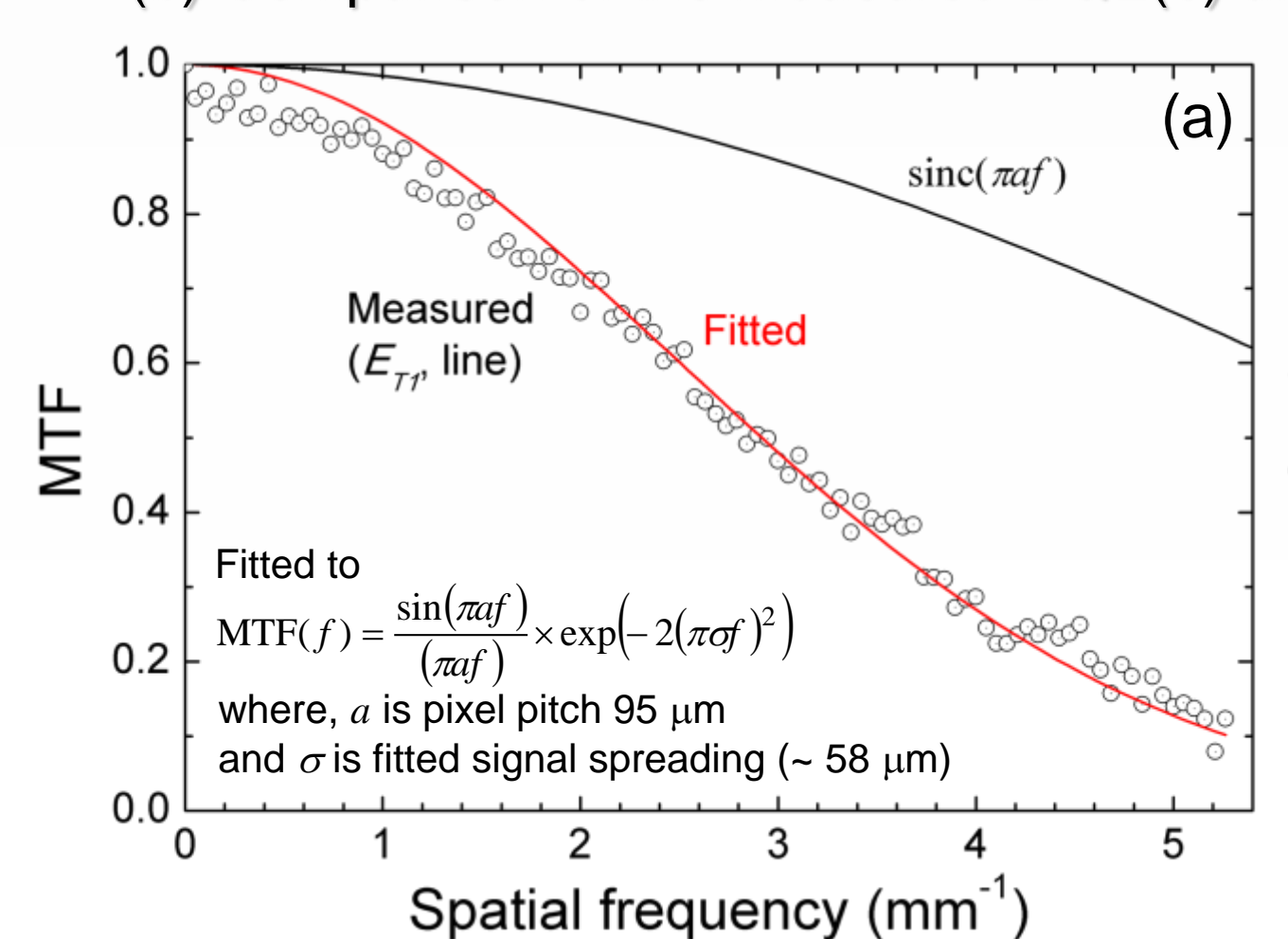
Results

- (a) Output signal responses as a function of detector entrance exposure for various threshold energies
- (b) Measured MTFs in two perpendicular directions (line and scan) for various threshold energies
- (c) Measured NPSs for $E_T=13$ keV in two perpendicular directions (line and scan) with respect to various entrance exposure levels
- (d) Measured NPSs for $E_T=22$ keV in two perpendicular directions (line and scan) with respect to various entrance exposure levels
- (e) Measured DQEs in two perpendicular directions (line and scan) for various threshold energies
- (f) DQEs extracted in line direction with respect to various exposure levels



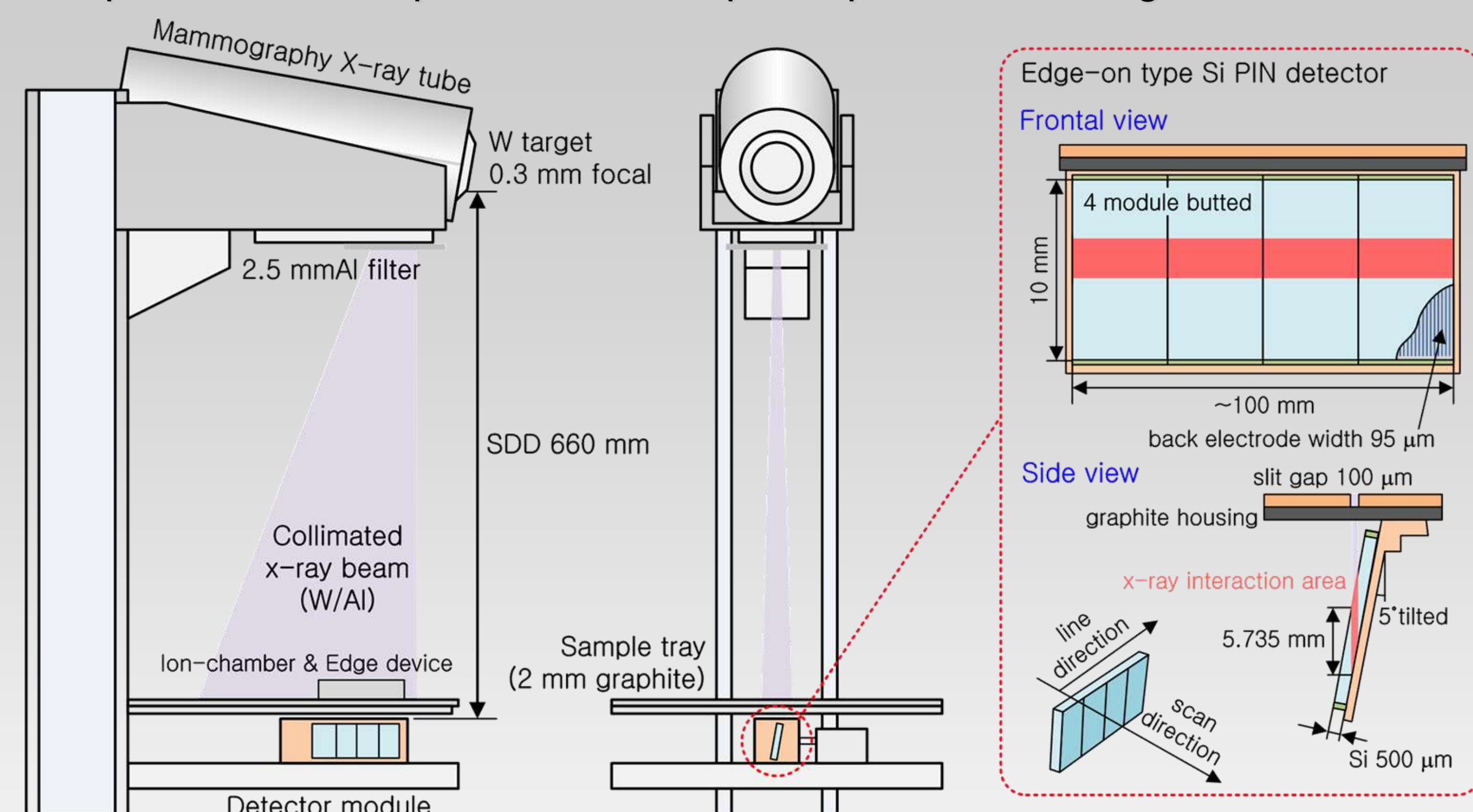
Regression analysis and calculated DQE(0)

- (a) Estimated charge sharing effect assuming the Gaussian charge diffusion model
- (b) Comparison of the measured DQE(0) and theoretical quantum efficiency



Materials and Methods

- Descriptions on the experimental set-up and photon-counting detector



IEC 62220-1-2 (2007)

※ Varian RAD-70B tube (W target with 0.76 mm Be window)

W/AI tube voltage	28 kVp	Adjusted voltage	28 kVp
Half value layer	0.83 mmAl	Measured HVL	0.839 mmAl
Added filter thick.	2.5 mmAl	Calculated SNR _{in} ²	6985 #/mm ² /μGy
Mandatory SNR _{in} ²	6575 #/mm ² /μGy	% difference (SNR _{in} ²)	5.87 %

※ Brief specifications of prototype detector unit

Detector type	line scanning	Material	Si (p-i-n)
Pixels per each module	256 pixels	# of energy bins	4 thresholds
Pixel pitch (line direction)	95 μm	Count rate (saturation)	0.5-0.7 Mcps
Dead gap btw. module	2 mm	Electronic noise	~ 200 e- rms
Collimator (slit) gap	100 μm	Energy resolution	~ 1.7 keV (FWHM)

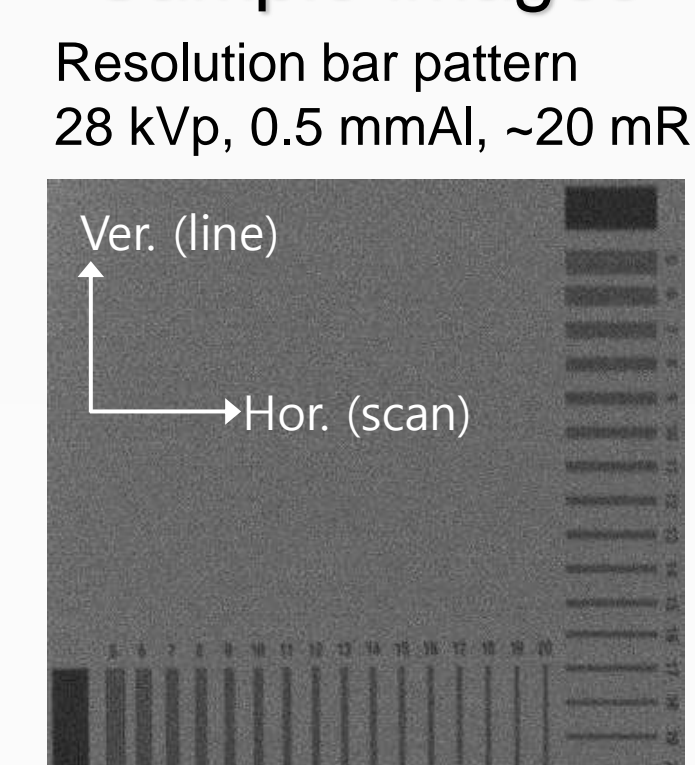
※ Definition of linear system DQE

$$DQE(f) = \frac{q^2 G^2 MTF^2(f)}{NPS(f)}$$

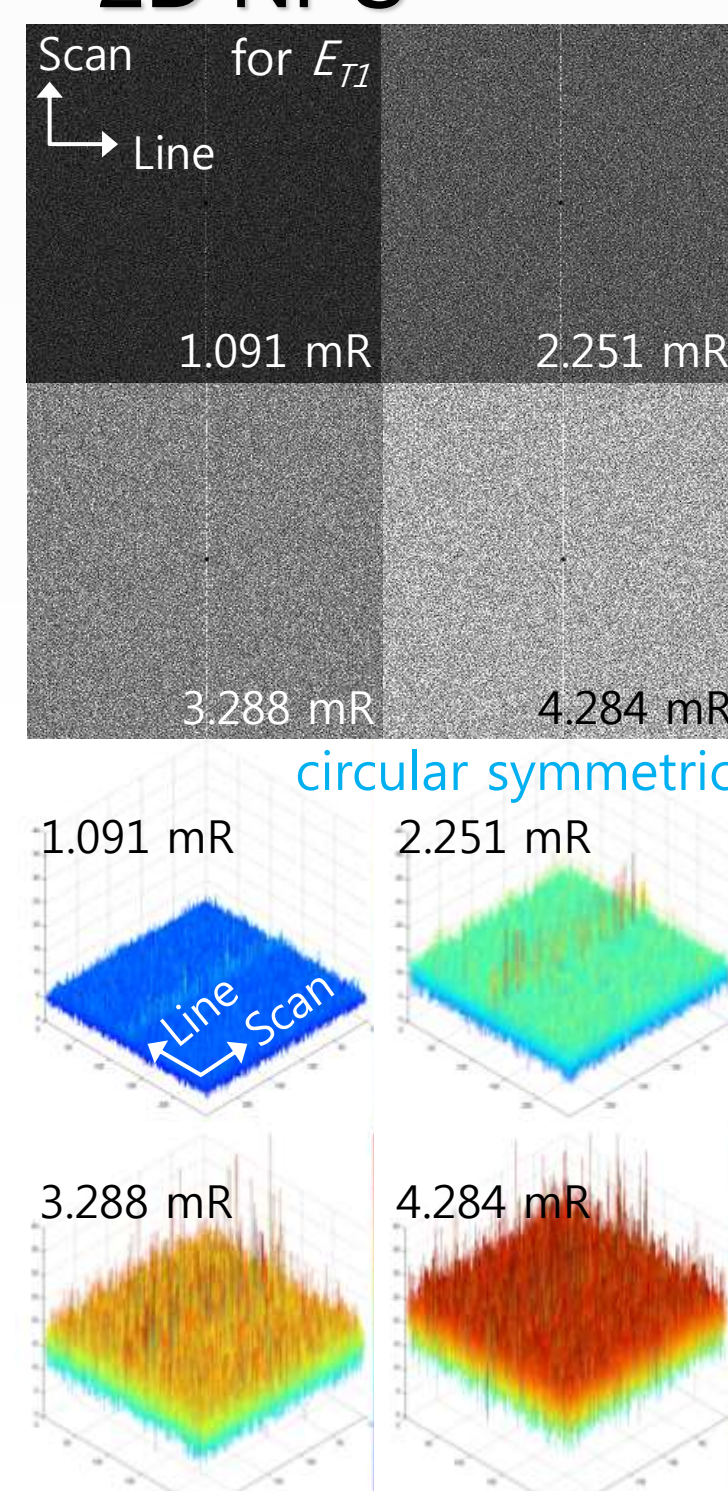
$$DQE(f) = \frac{\bar{d}^2 MTF^2(f)}{NPS(f) \bar{q}}$$

※ Threshold energy (E_T): 13, 15 and 22 keV
Counting time per scan line: 100 ms
Tray movement speed: 110 μm/scan

Sample images



2D NPS



Discussion and Summary

- In this study, we have systematically measured the imaging performance of a prototype silicon microstrip photon-counting detector under mammographic imaging condition.
- The measured MTF values are much lower than the sine cardinal function (ideal pixel MTF) of the physical pixel aperture, which implies that there exists an **additional signal spreading**, such as Compton scatter and charge sharing.
- We have modeled the signal spreading as a Gaussian model to perform the regression analysis. From the result, $\sigma = \sim 58 \mu\text{m}$ of **additional signal spreading** has been observed.
- The measured **DQE(0)** is much lower than the **theoretically calculated quantum efficiency** based on the Monte Carlo simulation. This would be explained by the **Swank noise factor** mainly due to the random charge sharing effect.
- According to the measurements of DQE with respect to various exposure levels, the additive electronic noise in the silicon microstrip photon-counting detector is negligible. Therefore, the silicon microstrip photon-counting detector has the **potential in low-dose imaging**.
- The overall imaging performances measured in this study are comparable to those of conventional commercial mammography detectors. *P. Monnin, Med. Phys. 34(3), 2007 & M. Aslund, Med. Phys. 34(6), 2007*